## Claims

## We claim:

- An apparatus used in monitoring the front surface of a wafer during a planarization process, comprising:
- a) a source for producing an interrogation signal;
- a plurality of probes adapted to transmit the interrogation signal to, and receive reflected interrogation signal from, a front surface of a wafer;
- c) a metrology instrument for measuring the interrogation signal; and
- d) a plurality of path ways for communicating the interrogation signal from the source to the probes and for communicating the reflected interrogation signal from the probes to the metrology instrument.
- An apparatus used in monitoring the front surface of a wafer during a planarization process, comprising:
- a) a light source for producing a light signal;
- a plurality of probes adapted to transmit the light signal to, and receive reflected light from, a front surface of a wafer;
- a metrology instrument for measuring the intensity of the reflected light; and
- a plurality of fiber optic cables for communicating the light signal from the light source to the probes and for communicating the reflected light from the probes to the metrology instrument.
- 3. The apparatus of claim 2, wherein the metrology instrument is a spectrometer.
- The apparatus of claim 3, wherein the probes and spectrometer are adapted for working with multi-frequency light.
- 5. The apparatus of claim 2, further comprising:
- e) a working surface for planarizing the front surface of the wafer:
- a carrier for retaining and pressing the front surface of the wafer against the working surface:
- g) a rotational motion generator adapted for rotating the carrier; and

- h) an orbital motion generator adapted for orbiting the working surface.
- 6. The apparatus of claim 5, wherein the working surface is a polishing pad.
- The apparatus of claim 6, wherein the plurality of probes extend through the polishing pad.
- The apparatus of claim 6, wherein the probes are positioned beneath the polishing pad to monitor a plurality of annular areas that substantially cover the front surface of the wafer.
- The apparatus of claim 6, wherein the probes transmit the light signal and receive the reflected light through the polishing pad.
- 10. The apparatus of claim 6, further comprising:
- i) a plurality of windows in the polishing pad above the probes.
- 11. The apparatus of claim 6, wherein the polishing pad is transparent above the probes.
- 12. The apparatus of claim 8, wherein adjacent annular areas on the front surface of the wafer overlap.
- 13. The apparatus of claim 8, wherein the carrier is adapted to place a first pressing force on a first annular area on the back surface of the wafer and a second pressing force on a second annular area on the back surface of the wafer.
- 14. A method for planarizing a front surface of a wafer comprising the steps of:
- a) pressing a front surface of a wafer against a working surface;
- b) generating relative motion between the front surface of the wafer and the working surface;
- transmitting a plurality of light signals to a plurality of bands on the front surface of the wafer:
- d) receiving a plurality of reflected light signals from the plurality of bands with a plurality of probes:
- e) communicating the reflected light from the plurality of probes to a metrology instrument;
- f) analyzing the plurality of reflected light signals from the plurality of bands; and
- g) altering the planarization process based on the analysis.

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- 15. The method of claim 14 wherein the planarization process is altered by adjusting the pressure in one or more zones of a multizone carrier.
- The method of claim 14 wherein the plurality of bands on the front surface of the wafer overlap.
- 17. The method of claim 14 wherein the generated relative motion comprises rotating the carrier and orbiting the working surface.
- 18. The method of claim 14 wherein the plurality of light signals comprise multiple frequencies.
- 19. The method of claim 14 wherein the metrology instrument comprises a spectrometer.